



## SONNENSCHNEN, NATH &amp; ROSENTHAL

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Chicago, IL 60606-1080  
312/876-8000

2815  
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MINOR RE APPLICATION OF: Minoru Sugawara, et al. ATTORNEY DOCKET NO. 09792909-4740  
SERIAL NO.: 09/733,474 GROUP ART UNIT: 2815  
FILED: December 8, 2000 EXAMINER: J. Nguyen  
FOR: "SEMICONDUCTOR AND FABRICATION METHOD THEREOF"

## AMENDMENT "B"

Hon. Assistant Commissioner of Patents  
Washington D.C. 20231

SIR:

Transmitted herewith is an amendment in the above-identified application.

☒ No additional claim fee is required.

The fee has been calculated as shown below.

CLAIMS AS AMENDED						
	(2) CLAIMS REMAINING AFTER AMENDMENT		(4) HIGHEST NO. PREVIOUSLY PAID FOR	(5) PRESENT EXTRA	(6) RATE	(7) ADDITIONAL FEE
TOTAL CLAIMS		MINUS	-		( ) X 9.00 ( ) X 18.00	
INDEP. CLAIMS		MINUS		1	( ) X 39.00 ( ) X 80.00	
Application amended to contain any multiple dependent claims not previously paid for.				( ) YES ( ) NO	( ) \$130.00 ( ) \$260.00 ONE TIME	
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT					\$0.00	

\* If the entry in Column 2 is less than the entry in Column 4, write "0" in Column 5

\*\* If the "Highest Number Previously Paid For" IN THIS SPACE is less than 20 write "20" in this space.

- ☒ Applicant petitions the Commissioner of Patents and Trademarks to extend this time for response to the Office Action dated February 20, 2002 for two month(s) so that the period for response is extended to July 20, 2002. The Commissioner is authorized to charge the fee of \$400.00 for the extension to Deposit Account No. 19-3140.
- ☐ A check in the amount of \$\_\_\_ is attached to cover the additional claim fee.
- ☐ A check for \$\_\_\_ accompanying attached Terminal Disclaimer under 37 C.F.R. §1.321.
- ☐ A check for \$\_\_\_ for Amendment Under 37 C.F.R. 1.312(b) is attached.
- ☒ The Commissioner is hereby authorized to charge the extension fee and any additional fees which may be required, or to credit any overpayment to account No. 19-3140. A duplicate of this sheet is enclosed.
- When phoning re this application, please call 312/876-8000 - Ext. 12578.

SONNENSCHNEN, NATH & ROSENTHAL

BY Kevin W. Gynn (Reg. No. 29,927)  
Kevin W. Gynn

## CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to the Assistant Commissioner of Patents, Washington, D.C. 20231 on July 22, 2002.

Kevin W. Gynn  
SIGNATURE  
July 22, 2002

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT(S) *7/22/02*  
Minoru Sugawara, et al.  
4740

ATTY DOCKET NO. 09792909-

SERIAL NO. 09/733,474

GROUP ART UNIT: 2815

FILING DATE: December 8, 2000

EXAMINER: J. Nguyen

INVENTION: "SEMICONDUCTOR AND FABRICATION METHOD  
THEREOF"

*#5/A*  
*Am d t*  
*J. McInnis*  
*8/8/02*

AMENDMENT "B"

Hon. Assistant Commissioner of Patents  
Washington, D.C. 20231

S I R:

This amendment is filed in response to the Office Action of February 20, 2002.  
Please reconsider the application in view of the amendment and remarks presented  
below.

The marked-up version of any amended text or claim appears in the  
accompanying Appendix.

IN THE CLAIMS

Please amend the claims as follows:

Please cancel claims 1-3 and add new claims 4-12 as follows:

*sub B1*  
*A1*

4. (New) A semiconductor device with p-channel and n-channel field  
effect devices formed on a common substrate, comprising:  
a silicon substrate with p-channel and n-channel field effect regions  
corresponding to said p-channel and n-channel field effect devices, respectively,  
said n-channel field effect region having a silicon-germanium buffer layer on  
said substrate, a silicon-germanium compound relax layer on said buffer layer, a first  
silicon layer formed on said relax layer and a second silicon epitaxial layer formed on  
said first silicon layer,

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